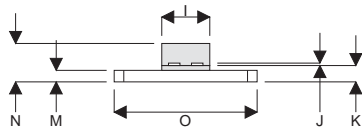
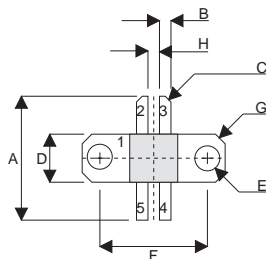


MECHANICAL DATA

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
5W – 28V – 1GHz  
PUSH-PULL**



DQ

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1  
 PIN 3 DRAIN 2 PIN 4 GATE 2  
 PIN 5 GATE 1

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- VHF/UHF COMMUNICATIONS  
from 50 MHz to 1 GHz

DIM	mm	Tol.	Inches	Tol.
A	16.38	0.26	0.645	0.010
B	1.52	0.13	0.060	0.005
C	45°	5°	45°	5°
D	6.35	0.13	0.250	0.005
E	3.30	0.13	0.130	0.005
F	14.22	0.13	0.560	0.005
G	1.27 x 45°	0.13	0.05 x 45°	0.005
H	1.52	0.13	0.060	0.005
I	6.35	0.13	0.250	0.005
J	0.13	0.02	0.005	0.001
K	2.16	0.13	0.085	0.005
M	1.52	0.13	0.060	0.005
N	5.08	MAX	0.200	MAX
O	18.90	0.13	0.744	0.005

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	35W
$BV_{DSS}$	Drain – Source Breakdown Voltage *	65V
$BV_{GSS}$	Gate – Source Breakdown Voltage *	±20V
$I_{D(sat)}$	Drain Current *	1A
$T_{stg}$	Storage Temperature	–65 to 150°C
$T_j$	Maximum Operating Junction Temperature	200°C

\* Per Side

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>PER SIDE</b>					
B <sub>V</sub> DSS	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0      I <sub>D</sub> = 10mA	65		V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0		1	mA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = 20V      V <sub>DS</sub> = 0		1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage*	I <sub>D</sub> = 10mA      V <sub>DS</sub> = V <sub>GS</sub>	1	7	V
g <sub>fs</sub>	Forward Transconductance*	V <sub>DS</sub> = 10V      I <sub>D</sub> = 1A	0.18		S
<b>TOTAL DEVICE</b>					
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 5W	13		dB
η	Drain Efficiency	V <sub>DS</sub> = 28V      I <sub>DQ</sub> = 0.2A	40		%
V <sub>SWR</sub>	Load Mismatch Tolerance	f = 1GHz	20:1		—
<b>PER SIDE</b>					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = -5V      f = 1MHz		12	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0      f = 1MHz		6	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0      f = 1MHz		0.5	pF

\* Pulse Test:    Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 5.0°C / W
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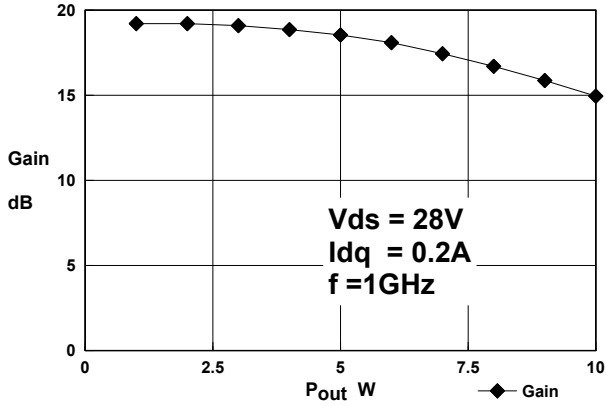


Figure 1 Output Power and Gain vs. Input power

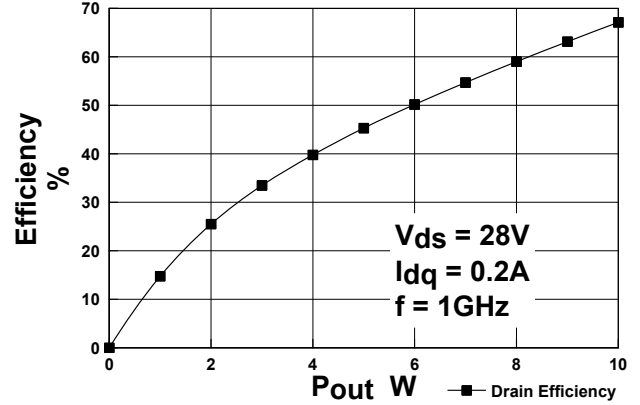


Figure 2 Output Power and Efficiency vs. Input Power

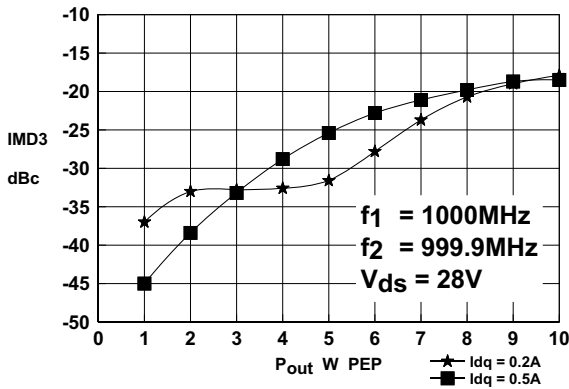


Figure 3 IMD Vs. Output Power.

OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
1000MHZ	1.1 - j2.5	5.1 - j17.1

Typical S Parameters

! Vds=28V, Idq=0.1A  
# MHZ S MA R 50

!Freq !MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
70	0.97	-36.4	15.8	156.6	0.017	67.2	0.91	-23.2
100	0.94	-48.0	14.1	146.3	0.021	58.1	0.88	-30.1
150	0.88	-65.3	12.3	129.9	0.027	45.5	0.81	-40.3
200	0.84	-78.5	10.2	114.7	0.029	34.8	0.77	-48.1
250	0.82	-88.4	8.8	106.0	0.029	28.1	0.75	-54.2
300	0.79	-97.1	7.7	98.3	0.029	27.3	0.73	-59.1
350	0.78	-105.5	6.9	88.5	0.028	22.2	0.72	-64.3
400	0.77	-113.3	6.0	84.5	0.026	24.2	0.71	-69.3
450	0.77	-121.8	5.4	77.8	0.024	23.3	0.70	-75.2
500	0.77	-128.9	4.9	75.3	0.022	29.6	0.70	-80.4
550	0.78	-136.7	4.6	68.3	0.020	35.0	0.70	-86.5
600	0.78	-144.0	4.4	65.4	0.020	46.6	0.70	-93.6
650	0.78	-150.8	4.0	57.2	0.020	57.6	0.70	-99.6
700	0.79	-156.7	3.7	52.3	0.022	68.5	0.71	-105.8
750	0.79	-160.9	3.4	46.7	0.025	76.6	0.70	-111.3
800	0.78	-164.2	3.0	41.4	0.028	81.6	0.69	-115.6
850	0.78	-166.3	2.7	39.5	0.032	87.8	0.68	-117.0
900	0.79	-168.5	2.6	38.4	0.036	92.3	0.68	-119.3
950	0.78	-170.3	2.5	36.8	0.044	97.4	0.70	-121.0
1000	0.79	-172.5	2.4	33.0	0.053	97.4	0.70	-124.2

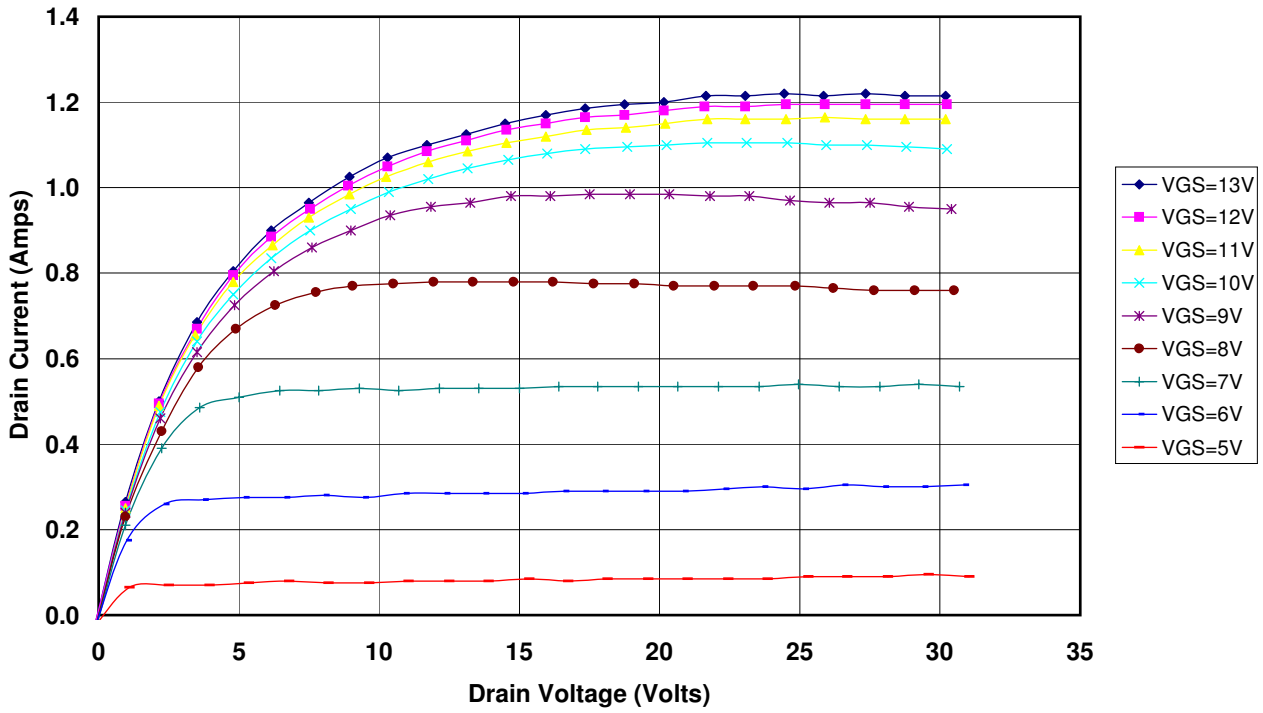


Figure 4 – Typical IV Characteristics.

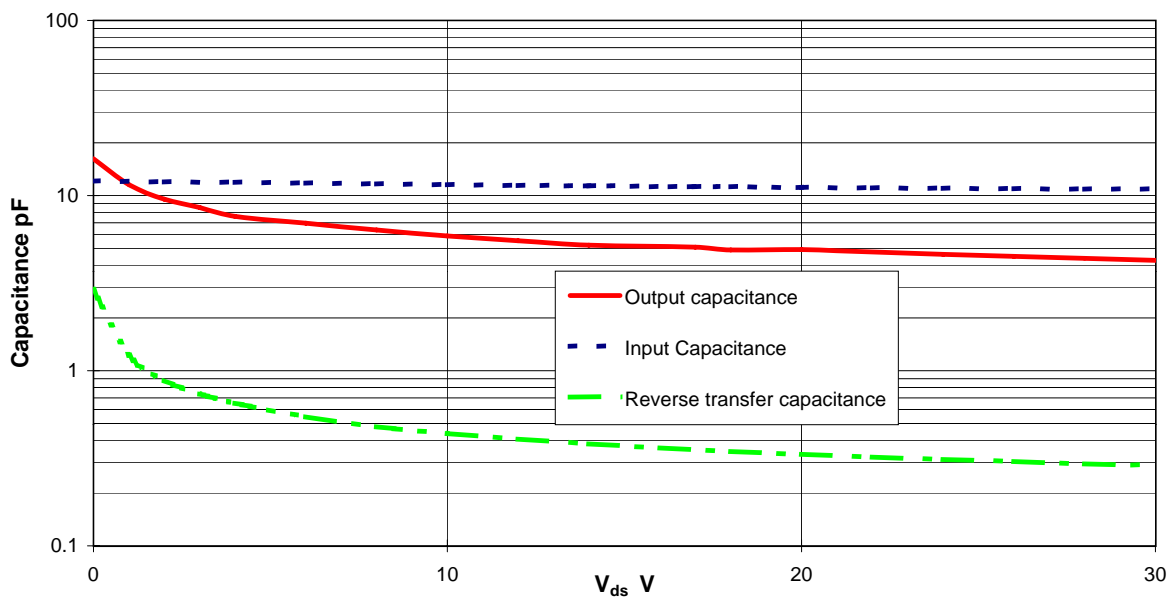
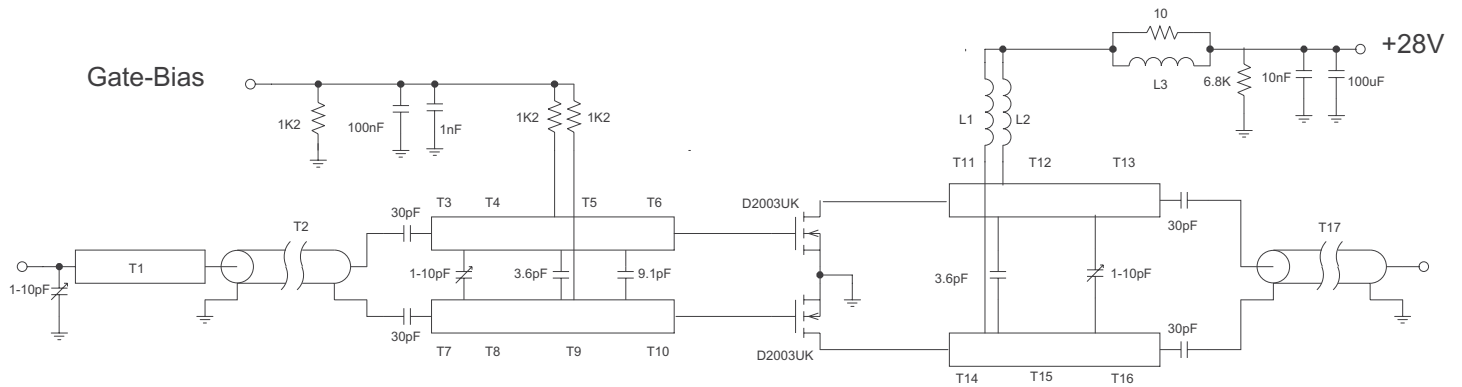


Figure 5 – Typical CV Characteristics.



## 1000MHz TEST FIXTURE

Substrate 0.8mm thick PTFE/glass

All microstrip lines  $W = 2.7\text{mm}$

T1	15.7
T2, T17	45mm 50 OHM UT 34 semi-rigid coax
T3, T7	7mm
T4, T8	15mm
T5, T9	7.6mm
T6, T10	8mm
T11, T14	8mm
T12, T15	11.2mm
T13, T16	7mm
L1, L2	6 turns 24swg enamelled copper wire, 3mm i.d.
L3	1.5 turn 24swg enamelled copper wire on Siemens B62152-A7X 2 hole core